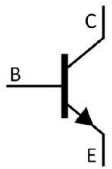


TO-92 NPN Silicon NPN transistor in a TO-92 Plastic Package.

2SB1238

High breakdown voltage high current complementary pair with 2SB1238.

Medium power amplifier applications.

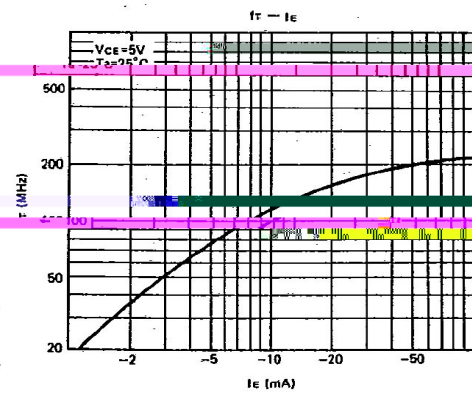
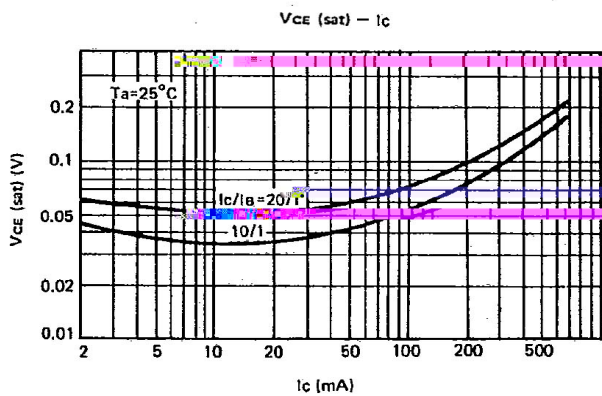
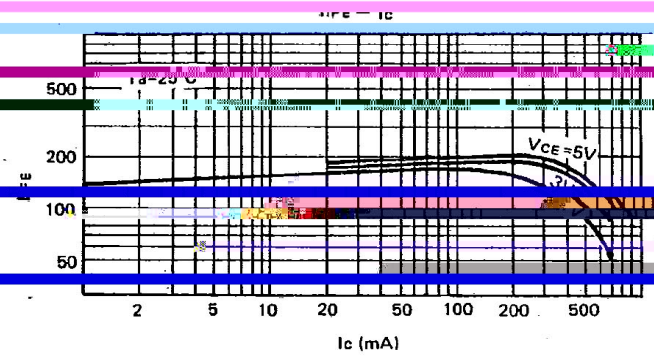
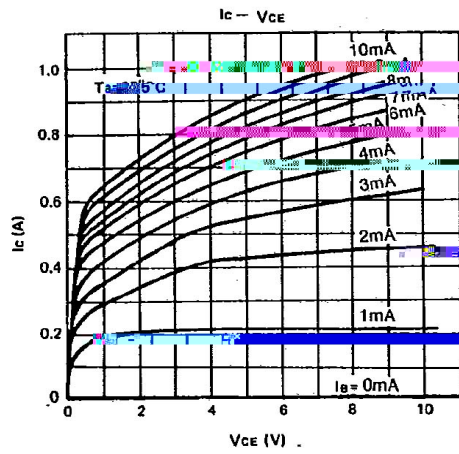
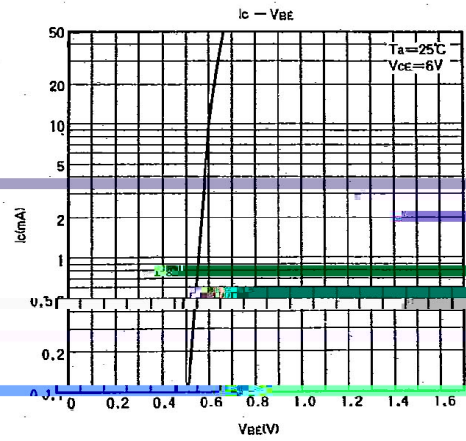
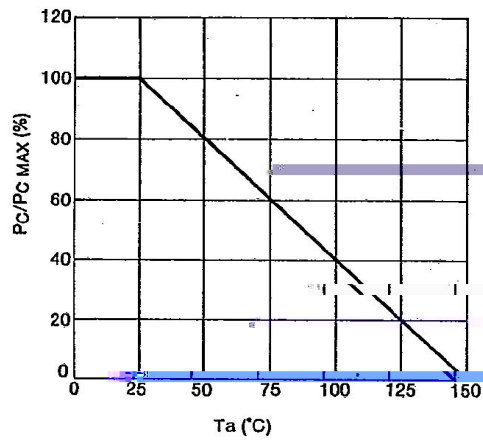


PIN1 Base PIN 2 Collector PIN 3 Emitter

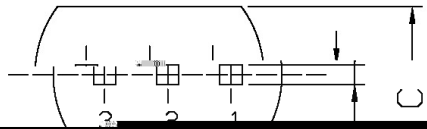
h_{FE} Classifications Symbol	Q	R
h_{FE} Range	120~270	180~390

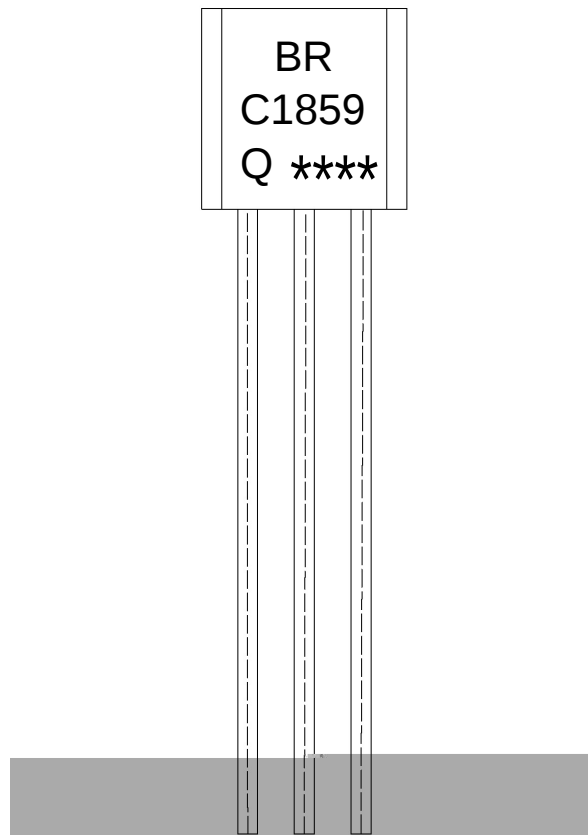
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	80	V
Collector to Emitter Voltage	V_{CEO}	80	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	0.7	A
Collector Power Dissipation	P_C	1.0	W
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55 150	°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=50\text{ A}$ $I_B=0$	80			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=2.0\text{mA}$ $I_B=0$	80			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=50\text{ A}$ $I_B=0$	5.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=50\text{V}$ $I_E=0$			0.5	A
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=4.0\text{V}$ $I_C=0$			0.5	A
DC Current Gain	h_{FE}	$V_{CE}=3.0\text{V}$ $I_C=0.1\text{A}$	120		390	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=500\text{mA}$ $I_B=50\text{mA}$		0.2	0.4	V
Transition Frequency	f_T	$V_{CE}=10\text{V}$ $f=100\text{MHz}$ $I_C=50\text{mA}$		120		MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=10\text{V}$ $f=1.0\text{MHz}$ $I_E=0$		10		pF



Unit: mm





BR:

C1859

Q: h_{FE}

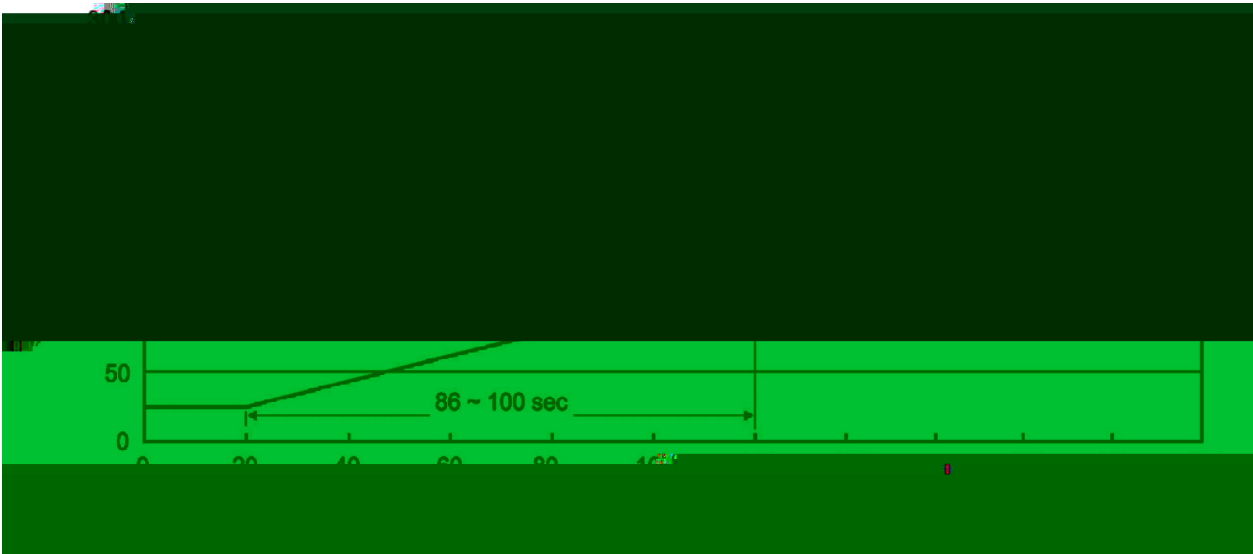
Note:

BR: Company Code.

C1859: Product Type.

Q: h_{FE} Classifications Symbol

****: Lot No. Code, code change with Lot No.



- 1

25 150

60 90sec;

2

255±5

5±0.5sec;

3

2 10

/sec.
- Note:

1.Preheating:25~150 , Time:60~90sec.

2.Peak Temp.:255±5 , Duration:5±0.5sec.

3. Cooling Speed: 2~10 /sec.

270±5

10±1 sec.

Temp:270±5℃

Time:10±1 sec

/ BULK

	Units 包装数量
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